TYN50W-1200T

SCR

Rev.02 - 27 August 2025 Product data sheet

1. General description

Planar passivated Silicon Controlled Rectifier in a TO247 plastic package intended for use in applications requiring very high inrush current capability and high thermal cycling performance.

2. Features and benefits

- High junction operating temperature capability ($T_{j(max)}$ = 150 °C)
- Very high current surge capability
- Planar passivated for voltage ruggedness and reliability
- High thermal cycling performance
- High voltage capability

3. Applications

- Line rectifying 50/60 Hz
- Softstart AC motor control
- Motor control
- Power converter
- AC power control
- Lighting and temperature control
- Uninterruptible Power Supply (UPS)
- Solid State Relay (SSR)
- Traction battery charging
- Hybrid PV Inverter

4. Quick reference data

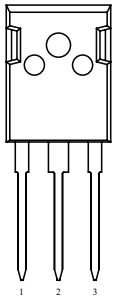
Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values	Unit
Absolute maximum rating					
V_{DRM}	repetitive peak off-state voltage			1200	V
V_{RRM}	repetitive peak reverse voltage			1200	V
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 131$ °C; Fig. 1; Fig. 2; Fig. 3		79	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)}$ = 25 °C; t_p = 10 ms; Fig. 4; Fig. 5		600	A
		half sine wave; $T_{j(init)}$ = 25 °C; t_p = 8.3 ms		660	A
T_j	junction temperature			150	°C

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 0.1 A; T_j = 25 °C; Fig. 7		-	-	80	mA
I_H	holding current	V_D = 12 V; T_j = 25 °C; Fig. 9		-	-	160	mA
V_T	on-state voltage	I_T = 50 A; T_j = 25 °C; Fig. 10		-	-	1.40	V
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 804 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		2000	-	-	V/µs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	 TO247	sym037
2	A	anode		
3	G	gate		
mb	A	mounting base; connected to anode		

6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
TYN50W-1200T	TO247	TYN50W-1200TQ	Tube	30	TO247P	09-Mar-2023
					TO247N	20-July-2016

7. Marking

Table 4. Marking codes

Type number	Marking codes	
	Assembly factory: P	Assembly factory: A
TYN50W-1200T	TYN50W 1200T PJPxxxx xx	TYN50W 1200T PJAxxxx xx

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
V_{DRM}	repetitive peak off-state voltage			1200	V
V_{RRM}	repetitive peak reverse voltage			1200	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{mb} \leq 131$ °C		50	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 131$ °C; Fig 1; Fig 2; Fig 3		79	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25$ °C; $t_p = 10$ ms; Fig 4; Fig 5		600	A
		half sine wave; $T_{j(init)} = 25$ °C; $t_p = 8.3$ ms		660	A
I^2t	I^2t for fusing	$t_p = 10$ ms; sine-wave pulse		1800	A^2s
dI_T/dt	rate of rise of on-state current	$I_G = 160$ mA		300	A/µs
I_{GM}	peak gate current			8	A
V_{RGM}	peak reverse gate voltage			5	V
P_{GM}	peak gate power			20	W
$P_{G(AV)}$	average gate power	over any 20 ms period		1	W
T_{stg}	storage temperature			-40 to 150	°C
T_j	junction temperature			-40 to 150	°C

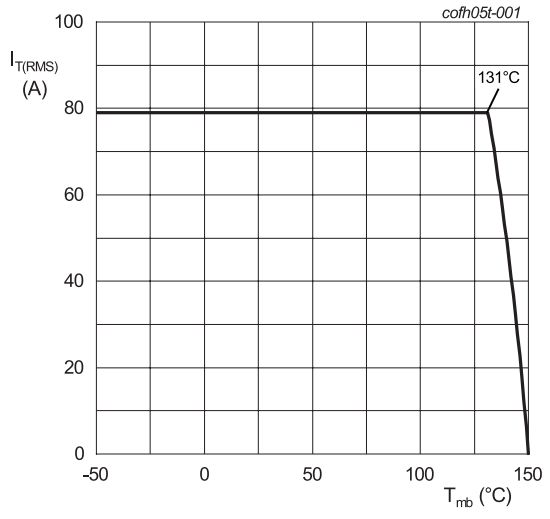
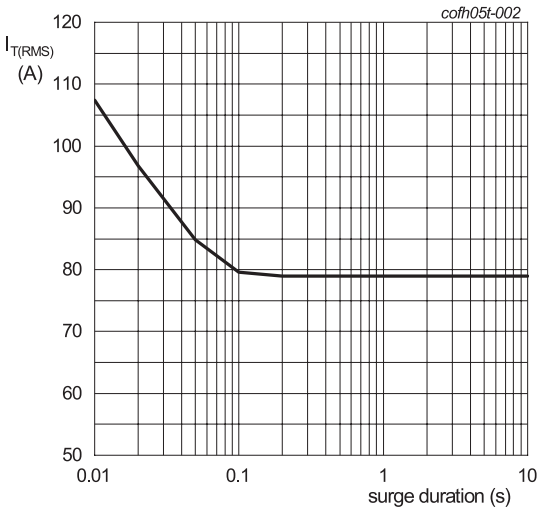


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



f = 50 Hz; T_{mb} = 131 °C

Fig. 2. RMS on-state current as a function of surge duration; maximum values

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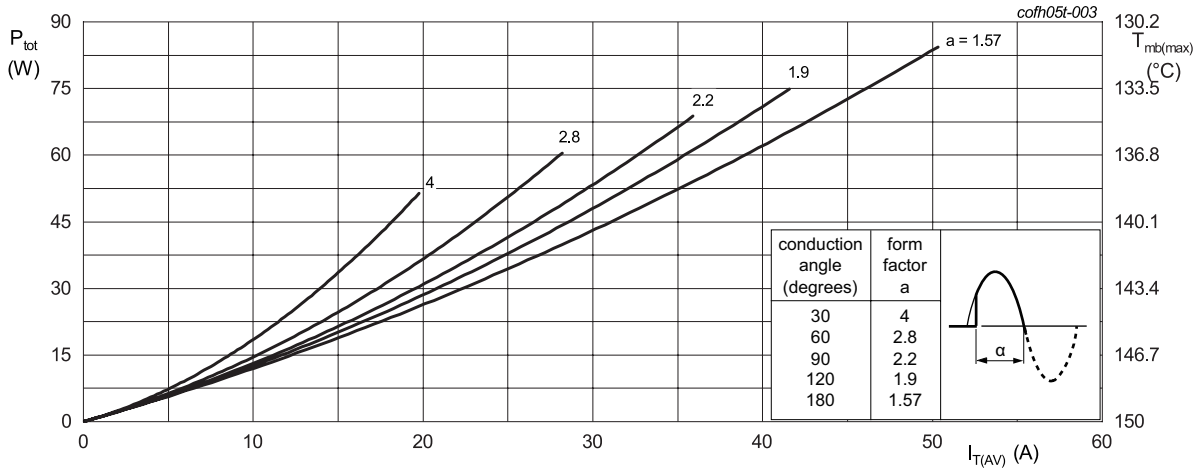
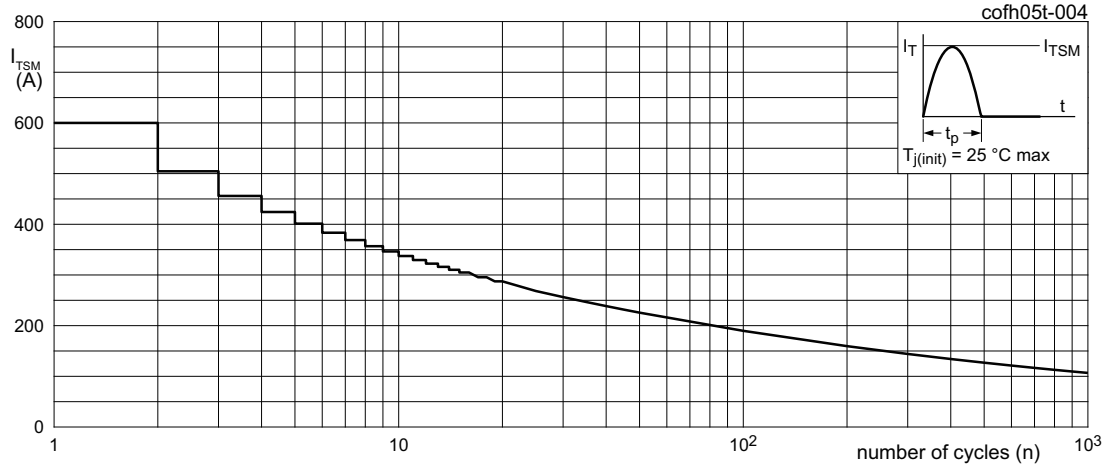


α = conduction angle

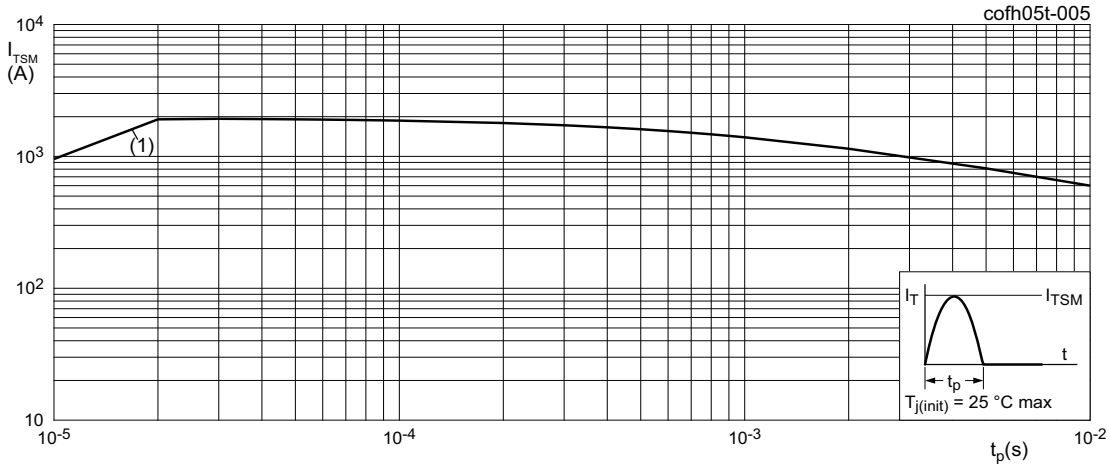
a = form factor = $I_{T(RMS)}$ / $I_{T(AV)}$

Fig. 3. Total power dissipation as a function of average on-state current; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



$t_p \leq 10$ ms

(1) dI_T/dt limit

Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

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9. Thermal & Mechanical characteristics

Table 6. Thermal & Mechanical characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig 6		-	-	0.22	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air		-	50	-	K/W
	Mounting torque	M3 screw mounting		0.55	-	0.8	Nm

Note: It is recommended that a metal washer is inserted between screw head and mounting tab. Do not use self-tapping screws.

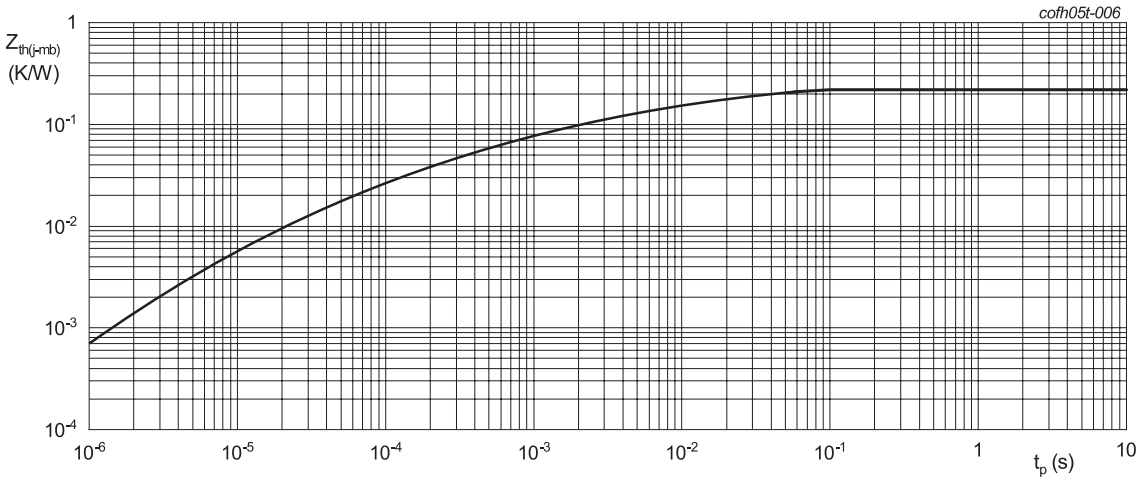

Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 0.1 A; T_j = 25 °C; Fig. 7; Fig. 8		-	-	80	mA
I_L	latching current	V_D = 12 V; I_G = 0.1 A; T_j = 25 °C; Fig. 9		-	-	180	mA
I_H	holding current	V_D = 12 V; T_j = 25 °C; Fig. 10		-	-	160	mA
V_T	on-state voltage	I_T = 50 A; T_j = 25 °C; Fig. 11		-	-	1.40	V
V_{GT}	gate trigger voltage	V_D = 12 V; I_T = 0.1 A; T_j = 25 °C; Fig. 12		-	0.7	1	V
		V_D = 800 V; I_T = 0.1 A; T_j = 150 °C		0.25	0.45	-	V
I_D	off-state current	V_D = 1200 V; T_j = 25 °C		-	-	10	µA
		V_D = 1200 V; T_j = 125 °C		-	-	3	mA
I_R	reverse current	V_D = 1200 V; T_j = 25 °C		-	-	10	µA
		V_D = 1200 V; T_j = 125 °C		-	-	3	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 804 V; T_j = 150 °C; Gate open circuit; (V_{DM} = 67% of V_{DRM}); exponential waveform		2000	-	-	V/µs
t_{gt}	gate-controlled turn-on time	I_{TM} = 50 A; V_D = 800 V; I_G = 0.1 A; dI_G/dt = 5 A/µs; T_j = 25 °C		-	2	-	µs
t_q	commutated turn-off time	V_{DM} = 804 V; T_j = 125 °C; I_{TM} = 50 A; V_R = 25 V; $(dI_T/dt)_M$ = 30 A/µs; dV_D/dt = 50 V/µs; $R_{GK(ext)}$ = 100 kΩ; (V_{DM} = 67% of V_{DRM})		-	150	-	µs

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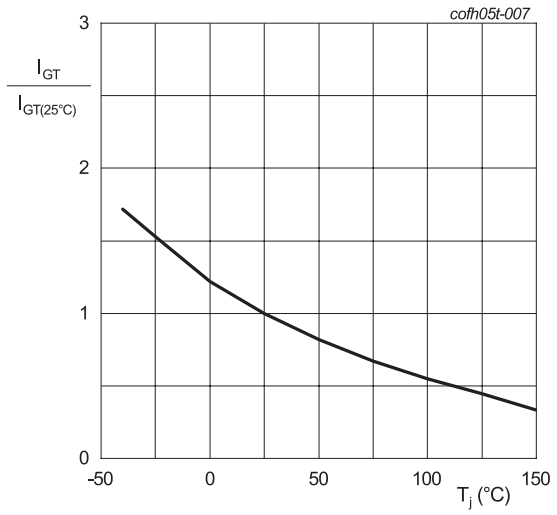


Fig. 7. Normalized gate trigger current as a function of junction temperature

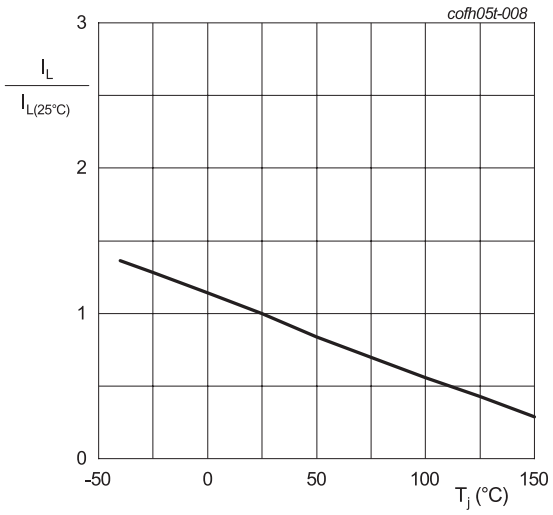


Fig. 8. Normalized latching current as a function of junction temperature

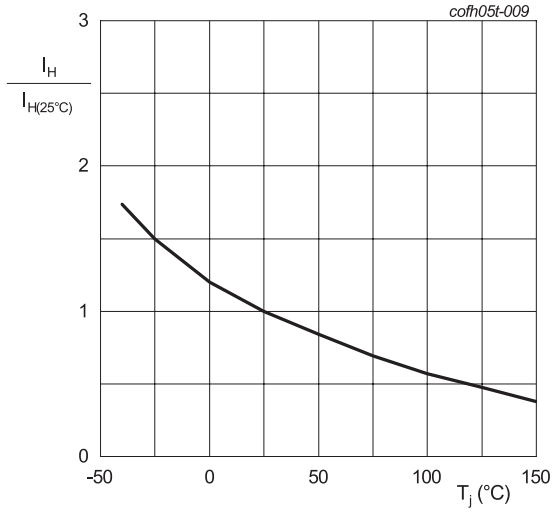
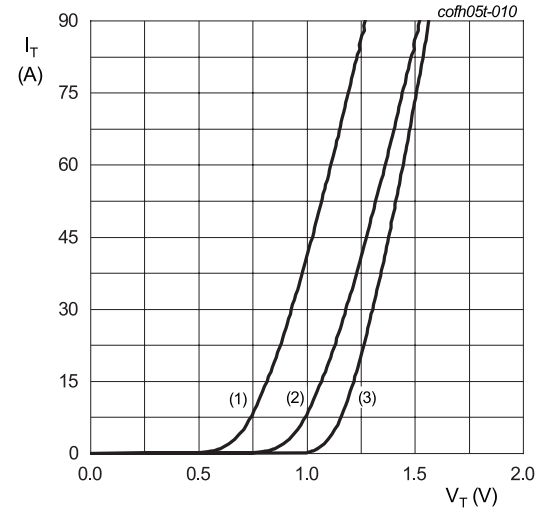


Fig. 9. Normalized holding current as a function of junction temperature



V_o = 1.080 V; R_s = 0.0048 Ω
(1) T_j = 150 °C; typical values
(2) T_j = 150 °C; maximum values
(3) T_j = 25 °C; maximum values

Fig. 11. On-state current as a function of on-state voltage

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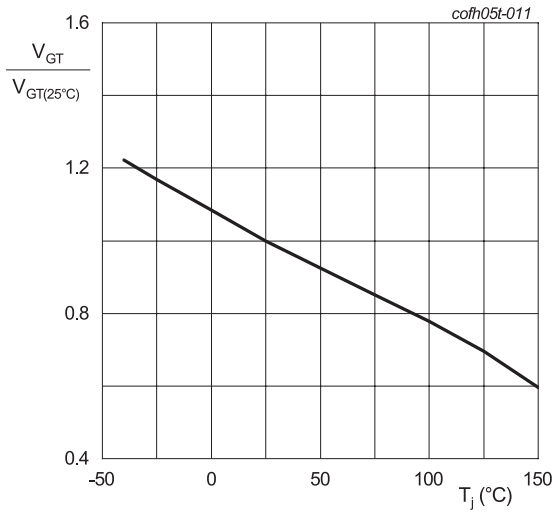

Fig. 11. Normalized gate trigger voltage as a function of junction temperature

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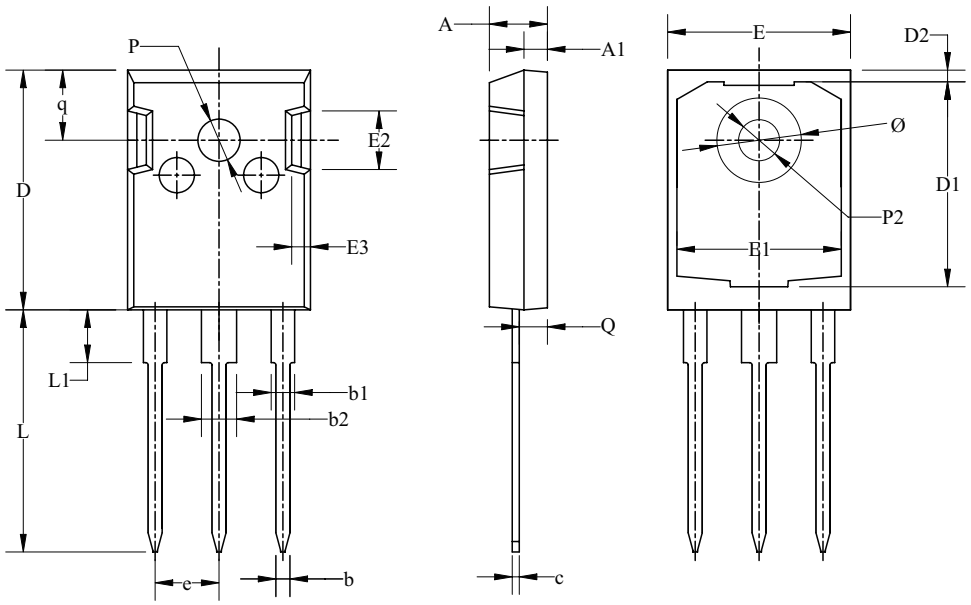
11. Package outline

Assembly factory: P

Plastic single-ended through-hole pack age; headsink mounted; 1 mounting hole; 3 leads TO-247 TO247



Dim	All Dimensions in Millimeters		
	Min	Typ	Max
A	4.70	4.95	5.20
A1	1.90	2.00	2.10
b	1.00	1.20	1.40
b1	1.80	2.00	2.20
b2	2.80	3.00	3.20
c	0.50	0.60	0.70
D	20.30	20.45	20.60
D1	17.28	17.48	17.68
D2	0.80	1.00	1.20
E	15.45	15.60	15.75
E1	13.82	14.02	14.22
E2	4.80	5.00	5.20
E3	1.40	1.60	1.80
e	5.45 BSC		
L	20.40	20.65	20.90
L1	4.25	4.50	4.75
P2	3.40	3.50	3.60
P	3.50	3.60	3.70
Q	2.20	2.40	2.60
q	5.78	5.98	6.18
Ø	7.10	7.19	7.30

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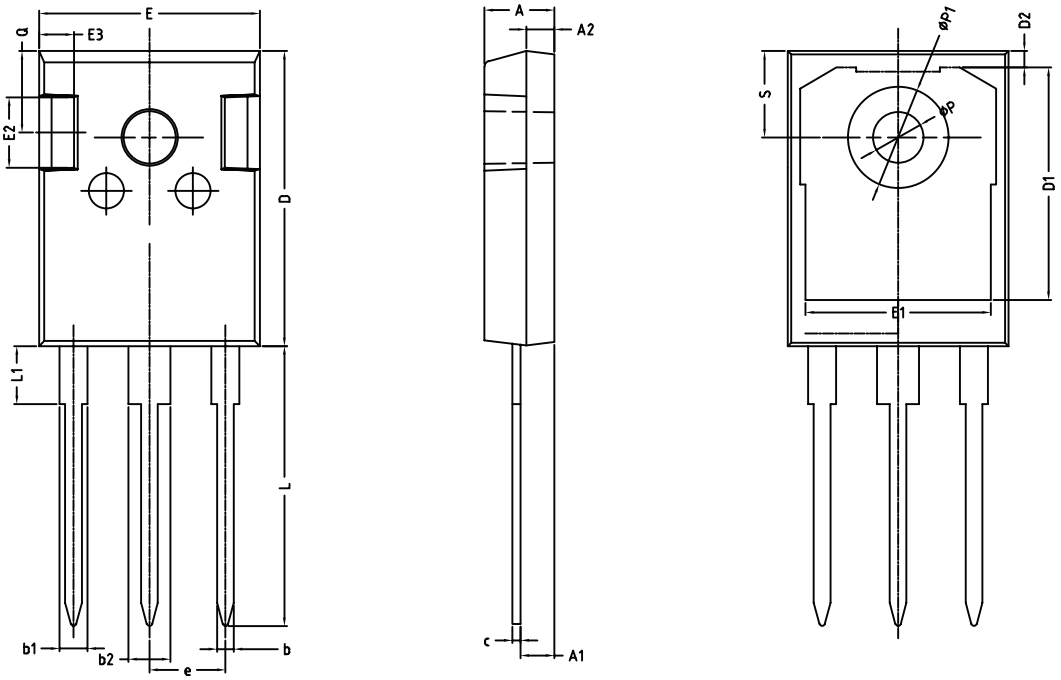
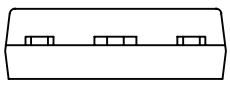
Assembly factory: A

Plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3-lead TO-247 SOT429N



TOP VIEW SIDE VIEW BOTTOM VIEW



SIDE VIEW

UNIT		A	A1	A2	b	b1	b2	c	D	D1	D2	E	E1	E2	E3	e	L	L1	P	P1	Q	S
mm	MAX	5.20	2.60	2.10	1.40	2.20	3.20	0.70	21.10	16.85	1.35	15.90	13.50	5.20	2.60	5.45	20.10	4.75	3.70	7.40	6.00	6.25
	NOM																					
	MIN	4.70	2.20	1.90	1.00	1.80	2.80	0.50	20.90	16.25	1.05	15.70	13.10	4.80	2.40		19.80	-	3.50	-	5.60	6.05

OUTLINE VERSION	REFERENCES				PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT429N		TO-247				

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Document status [1][2]	Product status [3]	Definition
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